

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company



N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS}(on)1=5.2m\Omega$ (typ.)
- 1.8V drive
- Halogen free compliance

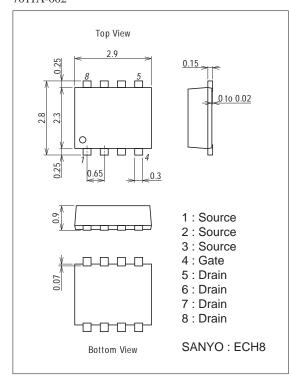
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	۱ _D		14	A
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	50	A
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-002



Product & Package Information

- Package : ECH8
- JEITA, JEDEC :-
- Minimum Packing Quantity : 3,000 pcs./reel

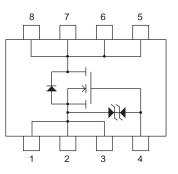
Packing Type : TL







Electrical Connection

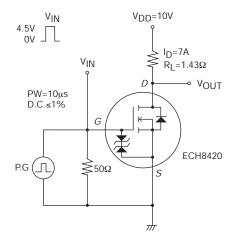


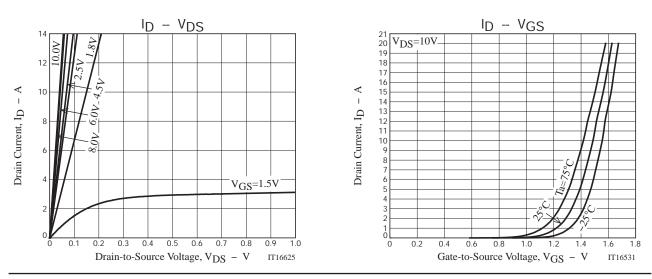
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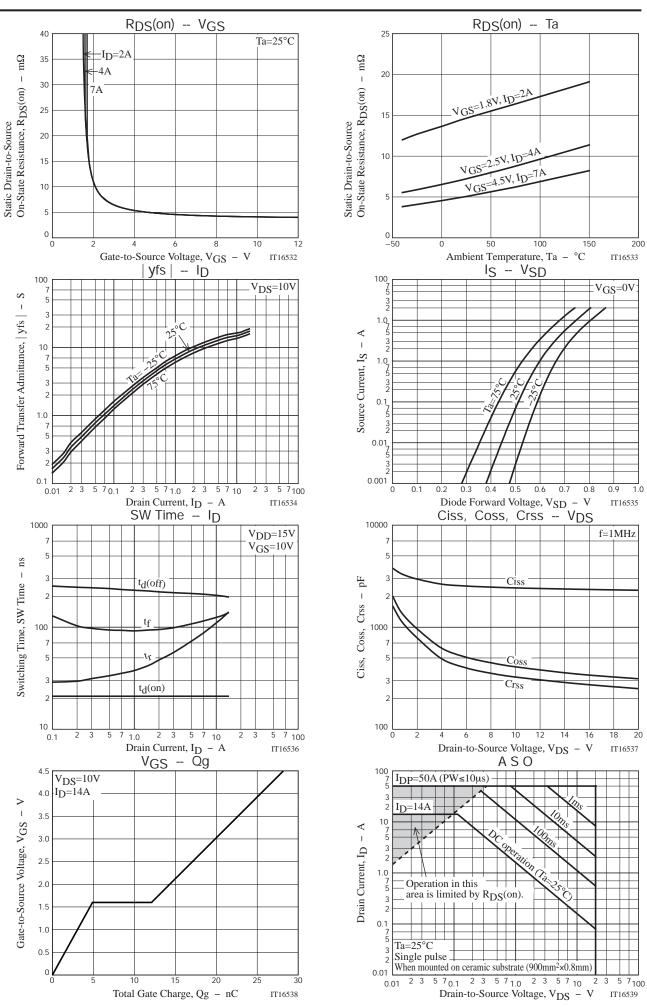
Electrical Characteristics at Ta=25°C

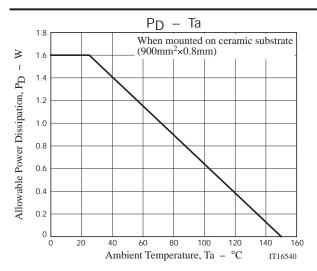
Parameter	Symbol	Conditions	Ratings			1.1
Parameter			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =7A		14.5		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=7A, VGS=4.5V		5.2	6.8	mΩ
	R _{DS} (on)2	ID=4A, VGS=2.5V		8	11.5	mΩ
	R _{DS} (on)3	ID=2A, VGS=1.8V		15	22.5	mΩ
Input Capacitance	Ciss			2430		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		410		pF
Reverse Transfer Capacitance	Crss			330		pF
Turn-ON Delay Time	t _d (on)			21		ns
Rise Time	tr	See specified Test Circuit.		88		ns
Turn-OFF Delay Time	t _d (off)			210		ns
Fall Time	tf			115		ns
Total Gate Charge	Qg			29		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =14A		4.8		nC
Gate-to-Drain "Miller" Charge	Qgd	1		8.7		nC
Diode Forward Voltage	V _{SD}	IS=14A, VGS=0V		0.75	1.2	V

Switching Time Test Circuit









Note on usage : Since the ECH8420 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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